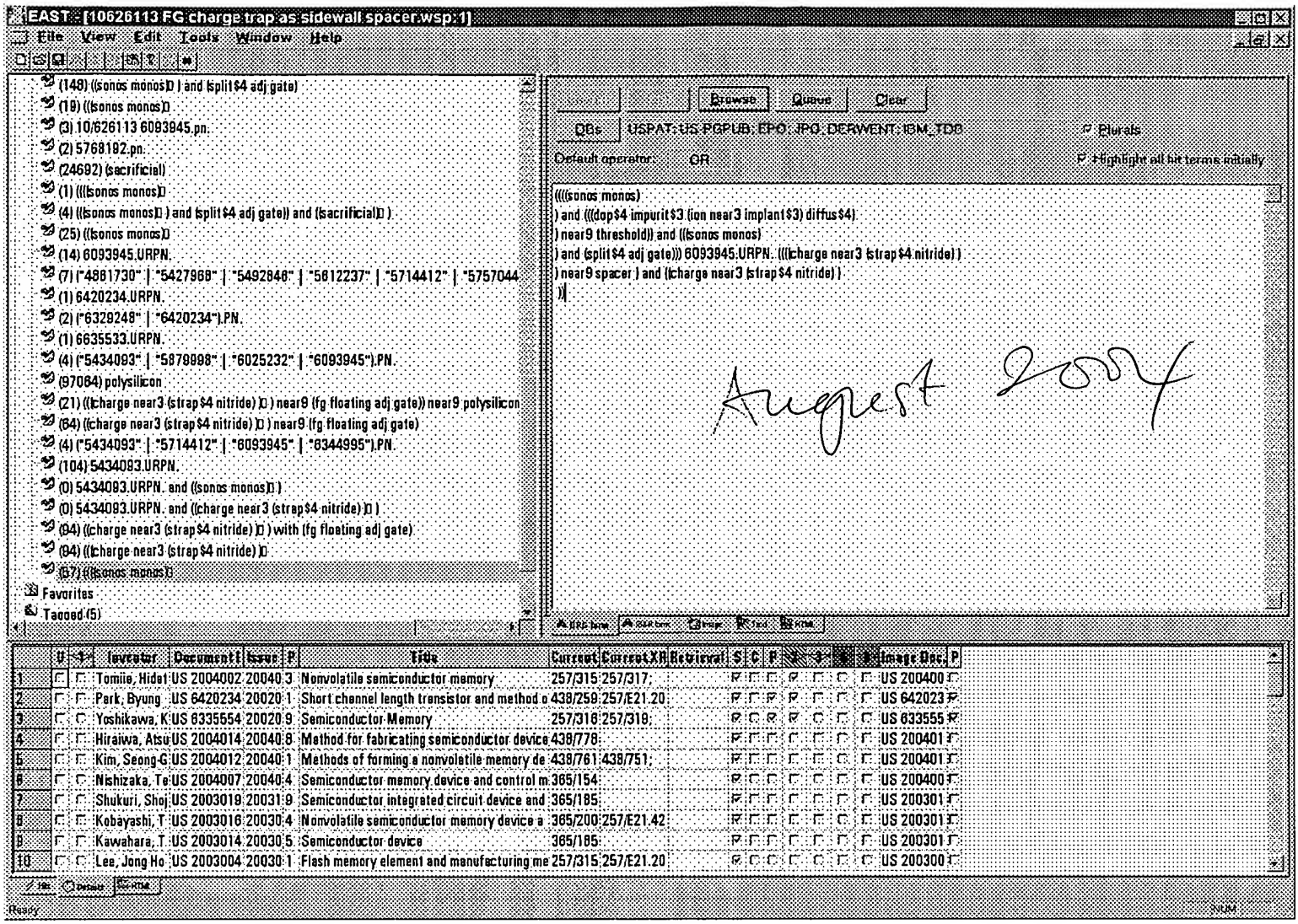
EAST - [10626113 FG charge trap as sidewall spacer.wsp:1]
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(148) ((sonos monos))) and (split$4 adj gate)
(19) ((sonos monos))
(3) 10/626113 6093945.pn.
(2) 5768192.pn.
(24692) (sacrificial)
(1) (((sonos monos))
(4) (((sonos monos))) and (split$4 adj gate)) and (sacrificial)))
(25) ((sonos monos))
(14) 6093945.URPN.
(7) ("4881730" | "5427968" | "5492846" | "5812237" | "5714412" | "5757044
(1) 6420234.URPN.
(2) ("6329248" | "6420234").PN.
(1) 6635533.URPN.
(4) ("5434093" | "5879998" | "6025232" | "6093945").PN.
(97084) polysilicon
(21) (((charge near3 (strap$4 nitride)))) near9 ((fg floating adj gate)) near9 polysilicon
(84) ((charge near3 (strap$4 nitride)))) near9 (fg floating adj gate)
(4) ("5434093" | "5714412" | "6093945" | "6344995").PN.
(104) 5434093.URPN.
(0) 5434093.URPN. and ((sonos monos))
(0) 5434093.URPN. and ((charge near3 (strap$4 nitride)))
(84) ((charge near3 (strap$4 nitride))) with (fg floating adj gate)
(84) ((charge near3 (strap$4 nitride)))
(57) ((sonos monos))
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((((sonos monos)
) and ((((dop$4 impurit$3 (ion near3 implant$3) diffus$4)
) near9 threshold)) and ((sonos monos)
) and (split$4 adj gate))) 6093945.URPN. ((((charge near3 (strap$4 nitride)))
) near9 spacer) and ((charge near3 (strap$4 nitride)))
))
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